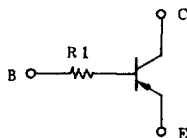


# RN2310, 2311

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT  
AND DRIVER CIRCUIT APPLICATIONS.

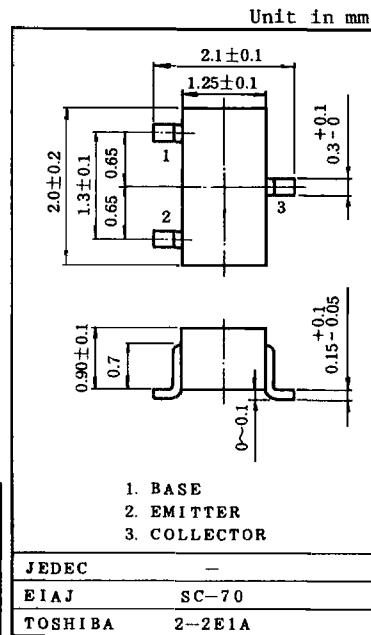
- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Complementary to RN1310, RN1311

## EQUIVALENT CIRCUIT



## MAXIMUM RATINGS (Ta=25°C)

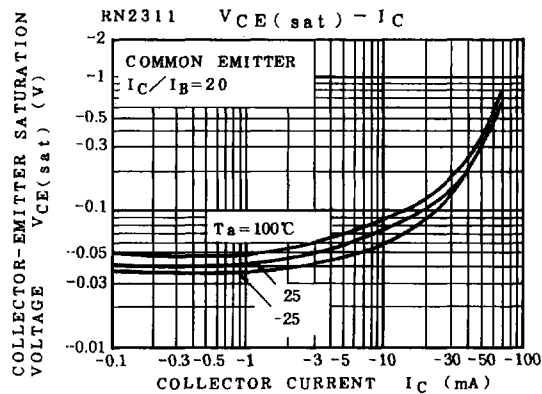
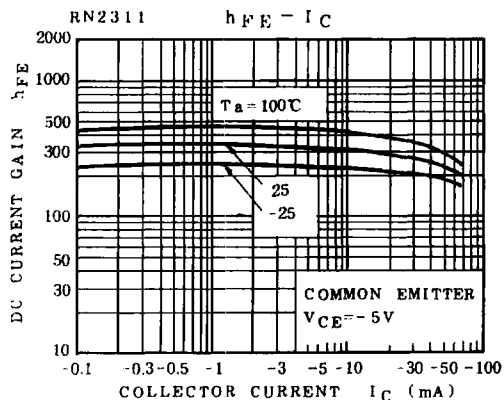
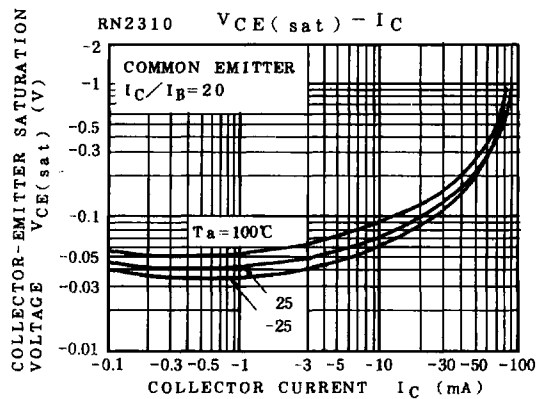
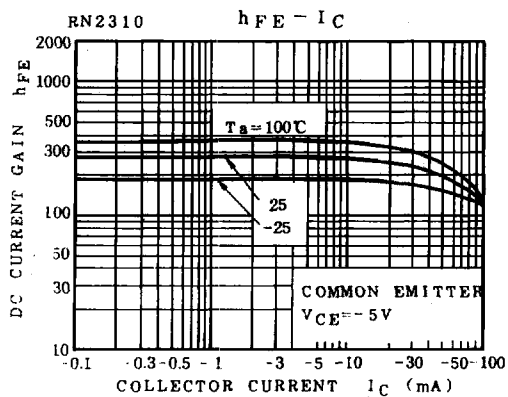
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	-50	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-50	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current	I <sub>C</sub>	-100	mA
Collector Power Dissipation	P <sub>C</sub>	100	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C

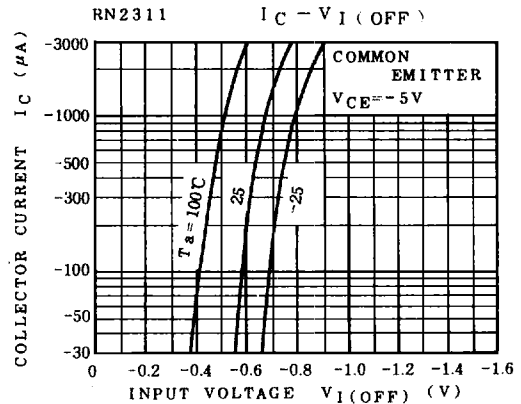
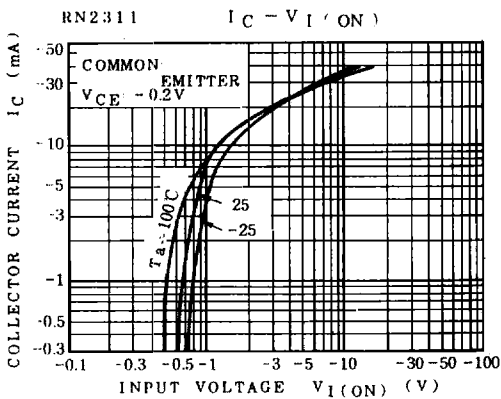
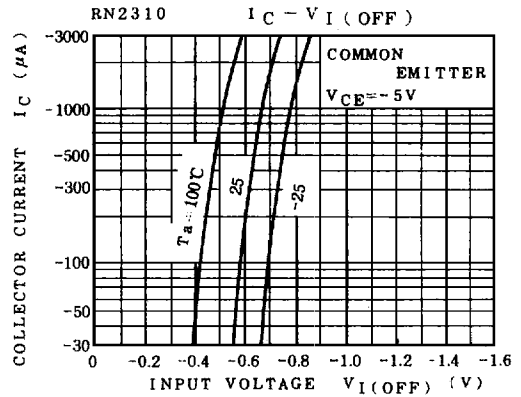
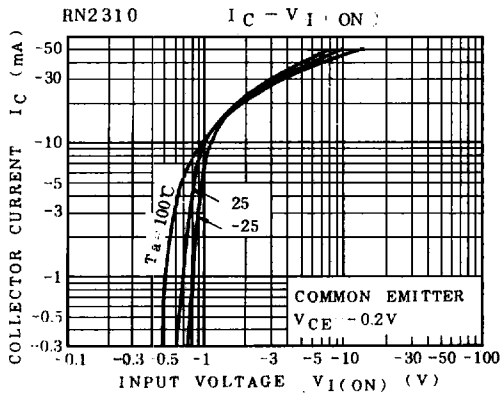


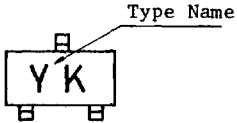
Weight: 0.006g

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0	-	-	-100	nA
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0	-	-	-100	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	120	-	400	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-5mA, I <sub>B</sub> =-0.25mA	-	-0.1	-0.3	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-5mA	-	200	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz	-	3	6	pF
Input Resistor	RN2310	R1	3.29	4.7	6.11	kΩ
	RN2311		7	10	13	





TYPE NAME	MARKING
RN2310	
RN2311	